IN THE SPECIFICATION

Please replace the Abstract with the Substitute Abstract attached hereto.

Please amend the paragraph beginning at page 8, line 8, as follows:

The results obtained on standard layers of Ni (in other words deposited continuously) are given in table II below.

Table I: Distribution parameters for particles obtained according to the invention

Ni thickness	2 nm	3 nm	5 nm	10 nm
Average	16 nm	17 nm	37.6	86.6
Standard deviation	0.7	0.7	0.5	0.6

~~Table I:~~

~~Distribution parameters for particles obtained according to the invention~~

Table II: Distribution parameters for particles obtained with standard Ni layers

Ni thickness	3 nm	10 nm
Average	54 nm	139 nm
Standard deviation	0.45	0.68

~~Table II:~~

~~Distribution parameters for particles obtained with standard Ni layers~~

Please amend the paragraph beginning at page 9, line 15, as follows:

Table III shows the result of treatment by hydrogen plasma at 300°C on a film deposited using the process according to the invention (in other words discontinuously) and using a standard process (in other words continuously).

Table III

Ni thickness	3 nm	3 nm	10 nm
Average	18 nm	No putting in	No putting in

		drops	drops
Standard deviation	0.5		
Ni deposition process	According to the invention	Standard	Standard

~~Table III~~

Please amend the paragraph beginning at page 10, line 11, as follows:

The layer 14 of Ni is made by an electron gun at ambient temperature using the device described above. An oxygen partial pressure equal to ~~3 x 10^{-5} mbars~~ 3 x 10^{-5} mbars is added during the deposition of Ni.

Please amend the paragraph beginning at page 10, line 17, as follows:

Table IV contains results related to the size of catalyst particles when an oxygen partial pressure is introduced during deposition.

Table IV

Ni thickness	3 nm	3 nm	10 nm	10 nm
O_2 partial pressure	0	3 x 10^{-5} mbars	0	3 x 10^{-5} mbars
Average	18 nm	13.5 nm	No putting in drops	24 nm
Standard deviation	0.5	0.5		0.5

~~Table IV~~